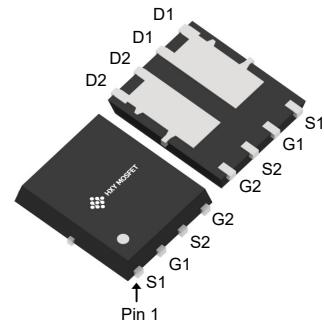




Description

The HXY30G20NF uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



DFN5X6B-8L

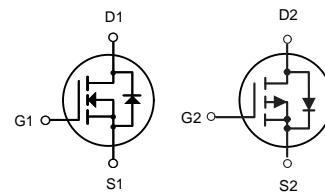
General Features

$V_{DS} = 30V$ $I_D = 16A$

$R_{DS(ON)} < 20m\Omega$ @ $V_{GS}=10V$

$V_{DS} = -30V$ $I_D = -14A$

$R_{DS(ON)} < 30m\Omega$ @ $V_{GS}=10V$



N-Channel

P-Channel

Application

Battery protection

Load switch

Uninterruptible power supply

Ordering Information

Product ID	Pack	Brand	Qty(PCS)
HXY30G20NF	DFN5X6B-8L	HXY MOSFET	5000

Absolute Maximum Ratings ($T_c=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating		Units
		N-Channel	P-Channel	
V_{DS}	Drain-Source Voltage	30	-30	V
V_{GS}	Gate-Source Voltage	± 20	± 20	V
$I_D @ T_c=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	16	-14	A
$I_D @ T_c=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	10	-10	A
I_{DM}	Pulsed Drain Current	46	-40	A
EAS	Single Pulse Avalanche Energy	28	66	mJ
$P_D @ T_c=25^\circ C$	Total Power Dissipation	15	21.3	W
$P_D @ T_A=100^\circ C$	Total Power Dissipation	5	4.8	W
T_{STG}	Storage Temperature Range	-55 to 150	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	---	45	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case	---	5	$^\circ C/W$



N-Channel Electrical Characteristics (T_J=25°C , unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	30	---	---	V
△BV _{DSS} /△T	BVDSS Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.023	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =10A	---	14	20	mΩ
		V _{GS} =4.5V , I _D =6A	---	20	25	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.0	---	2.5	V
△V _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-4.2	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =24V , V _{GS} =0V , T _J =25°C	---	---	1	uA
		V _{DS} =24V , V _{GS} =0V , T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V , I _D =10A	---	14	---	S
R _g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz	---	2.3	---	Ω
Q _g	Total Gate Charge (4.5V)	V _{DS} =20V , V _{GS} =4.5V , I _D =10A	---	5	---	nC
Q _{gs}	Gate-Source Charge		---	1.11	---	
Q _{gd}	Gate-Drain Charge		---	2.61	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =12V , V _{GS} =10V , R _G =3.3Ω I _D =6A	---	7.7	---	ns
T _r	Rise Time		---	46	---	
T _{d(off)}	Turn-Off Delay Time		---	11	---	
T _f	Fall Time		---	3.6	---	
C _{iss}	Input Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz	---	416	---	pF
C _{oss}	Output Capacitance		---	62	---	
C _{rss}	Reverse Transfer Capacitance		---	51	---	
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V , Force Current	---	---	16	A
I _{SM}	Pulsed Source Current ^{2,5}		---	---	30	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =1A , T _J =25°C	---	---	1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width \leq 300us , duty cycle \leq 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=12.7A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



P-Channel Electrical Characteristics ($T_J=25^\circ C$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to $25^\circ C, I_D=-1mA$	---	-0.021	---	$^\circ C$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V, I_D=-8A$	---	25	30	$m\Omega$
		$V_{GS}=-4.5V, I_D=-6A$	---	30	35	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.0	---	-2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-4.2	---	$mV/^\circ C$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-24V, V_{GS}=0V, T_J=25^\circ C$	---	---	1	uA
		$V_{DS}=-24V, V_{GS}=0V, T_J=55^\circ C$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-5V, I_D=-8A$	---	12.6	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1MHz$	---	15	---	Ω
Q_g	Total Gate Charge (-4.5V)	$V_{DS}=-20V, V_{GS}=-4.5V, I_D=-6A$	---	9.8	---	nC
Q_{gs}	Gate-Source Charge		---	2.2	---	
Q_{gd}	Gate-Drain Charge		---	3.4	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-24V, V_{GS}=-10V, R_G=3.3\Omega, I_D=-1A$	---	16.4	---	ns
T_r	Rise Time		---	20.2	---	
$T_{d(off)}$	Turn-Off Delay Time		---	55	---	
T_f	Fall Time		---	10	---	
C_{iss}	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V, f=1MHz$	---	930	---	pF
C_{oss}	Output Capacitance		---	148	---	
C_{rss}	Reverse Transfer Capacitance		---	115	---	
I_s	Continuous Source Current ^{1,5}	$V_G=V_D=0V, \text{Force Current}$	---	---	-14	A
I_{SM}	Pulsed Source Current ^{2,5}		---	---	-24	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_s=-1A, T_J=25^\circ C$	---	---	-1.2	V

Note :

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
2. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
3. The EAS data shows Max. rating . The test condition is $V_{DD}=-25V, V_{GS}=-10V, L=0.1mH, I_{AS}=-30A$
4. The power dissipation is limited by $150^\circ C$ junction temperature
5. The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



N-Channel Typical Characteristics

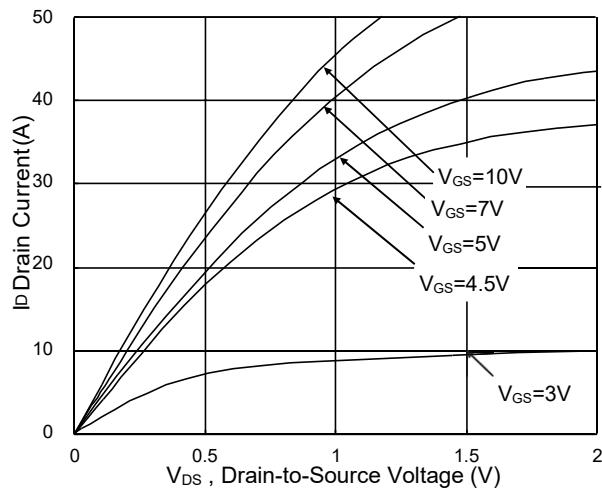


Fig.1 Typical Output Characteristics

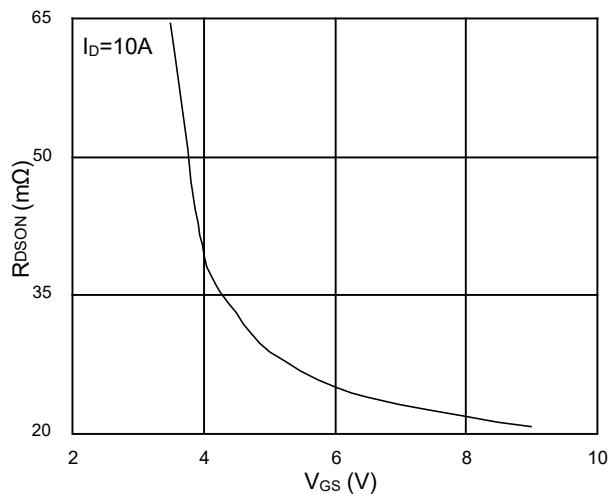


Fig.2 On-Resistance vs. Gate-Source

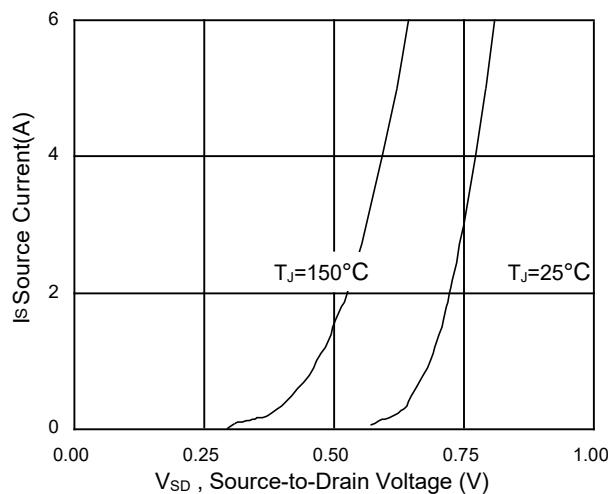


Fig.3 Forward Characteristics Of Reverse

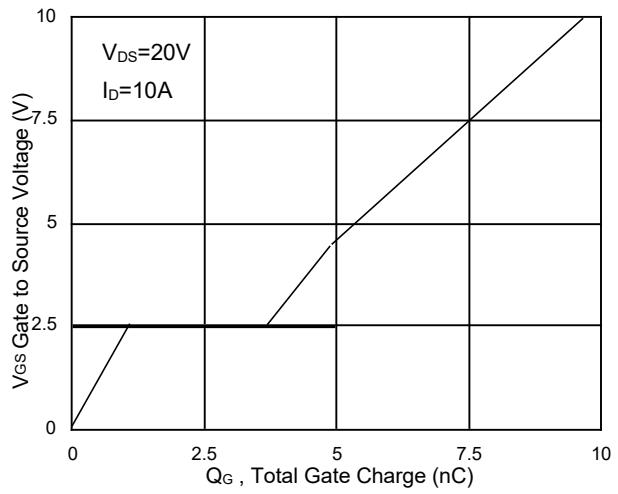


Fig.4 Gate-Charge Characteristics

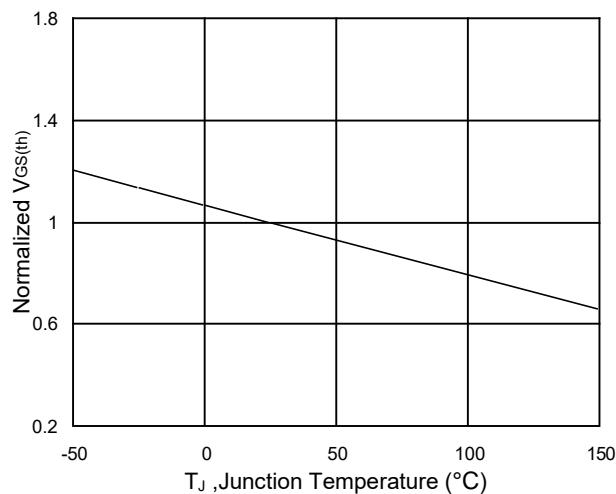


Fig.5 Normalized V_{GS(th)} vs. T_J

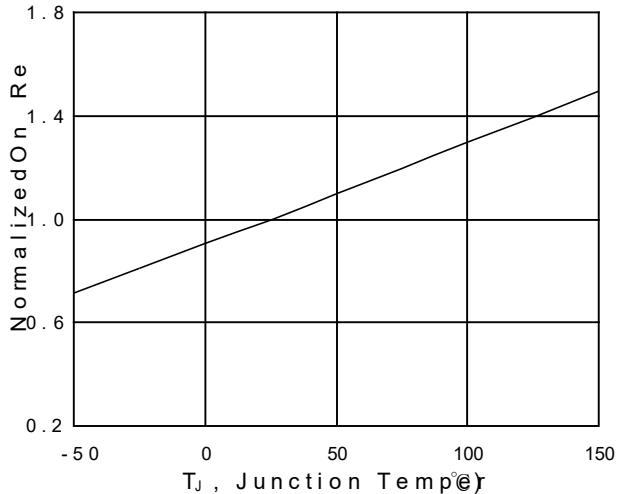


Fig.6 Normalized R_{DSON} vs. T_J

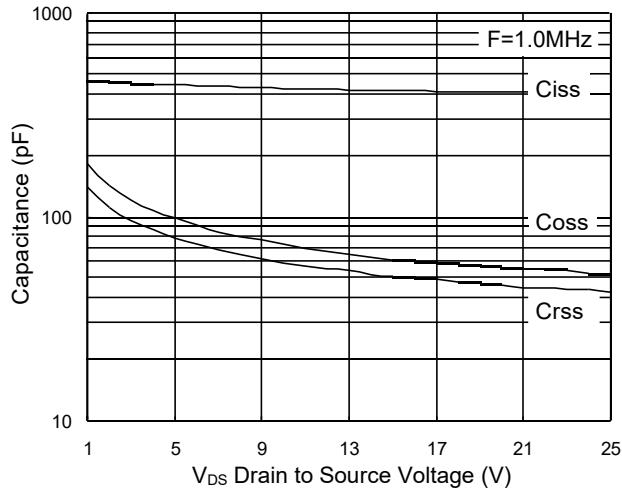


Fig.7 Capacitance

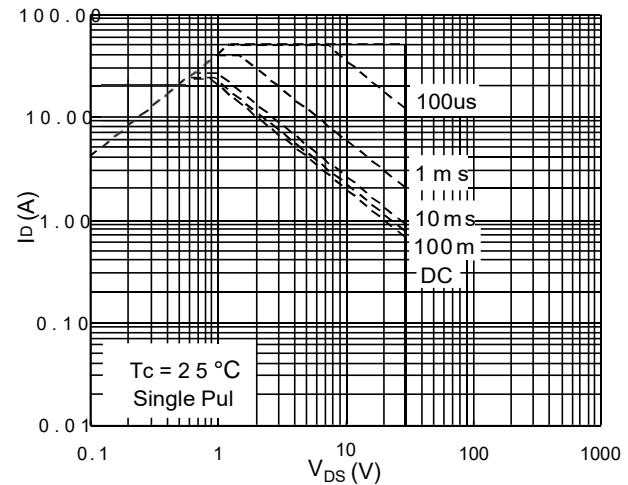


Fig.8 Safe Operating Area

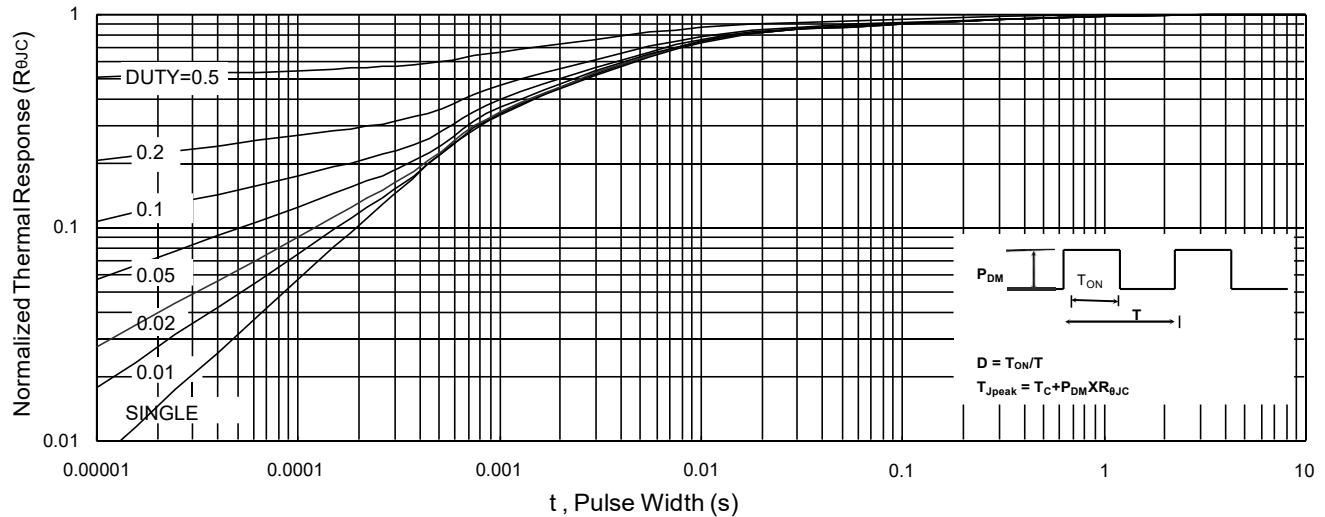
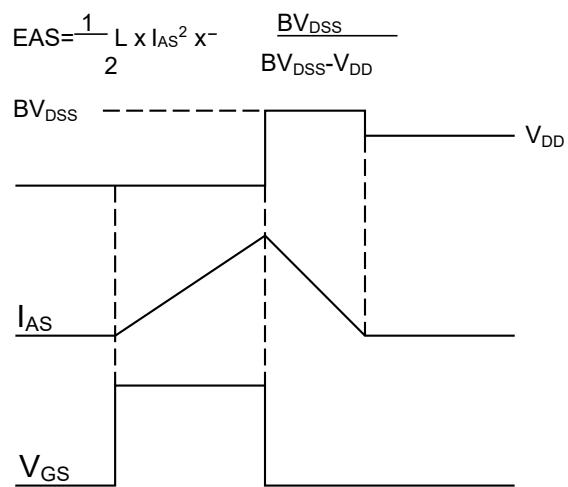
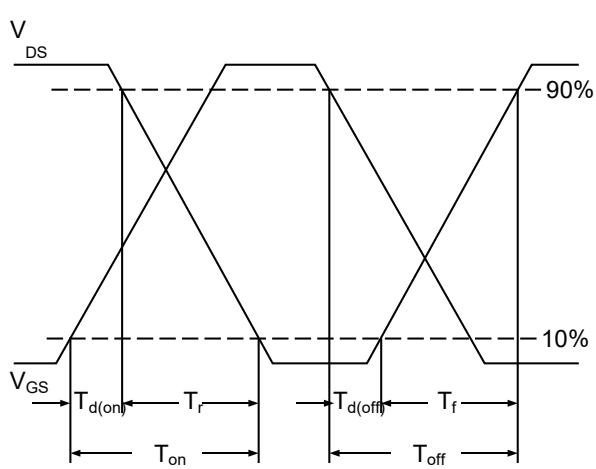


Fig.9 Normalized Maximum Transient Thermal Impedance





P-Channel Typical Characteristics

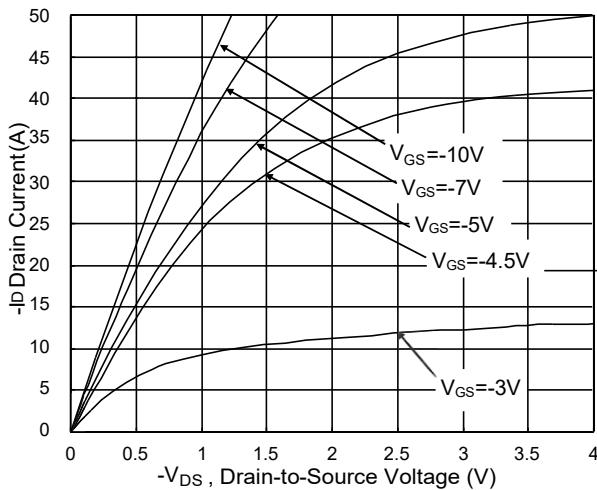


Fig.1 Typical Output Characteristics

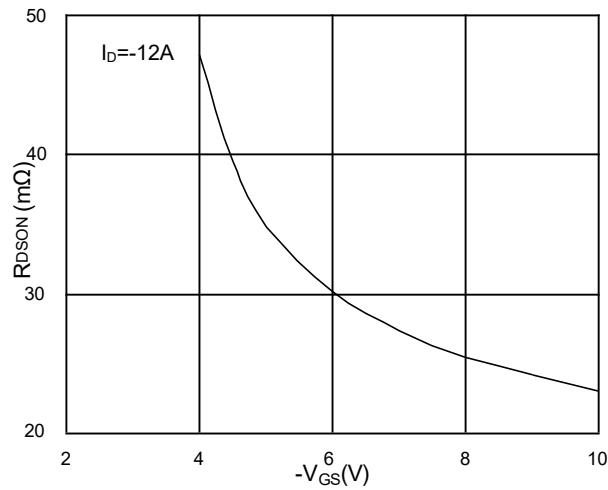


Fig.2 On-Resistance v.s Gate-Source

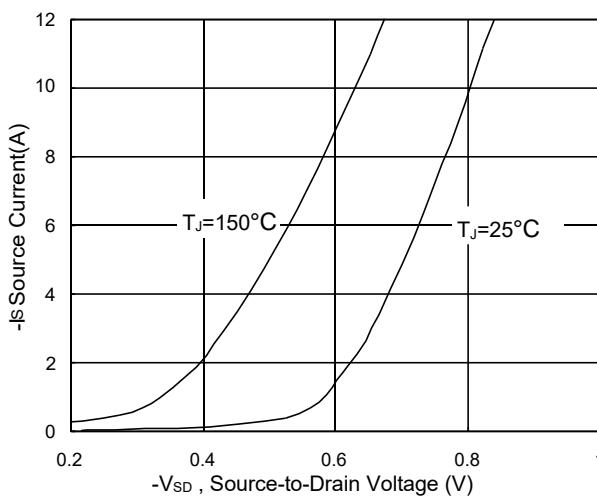


Fig.3 Forward Characteristics Of Reverse

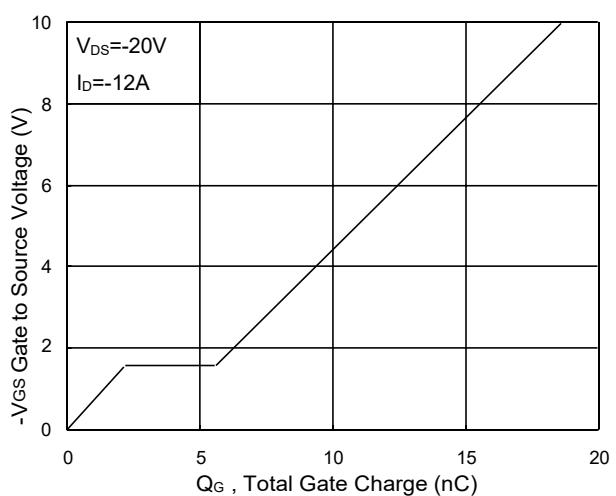


Fig.4 Gate-Charge Characteristics

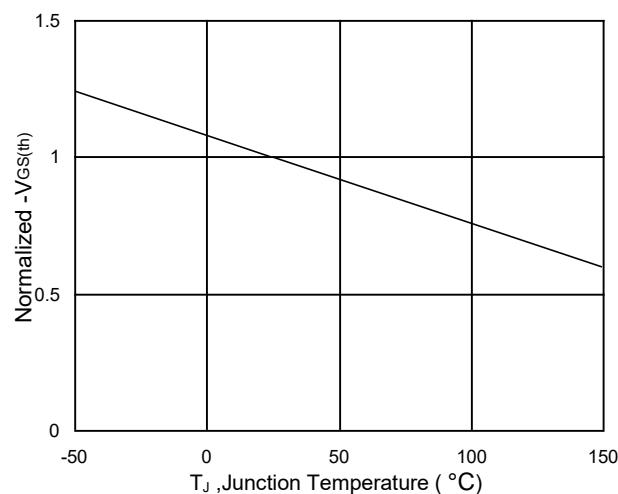


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

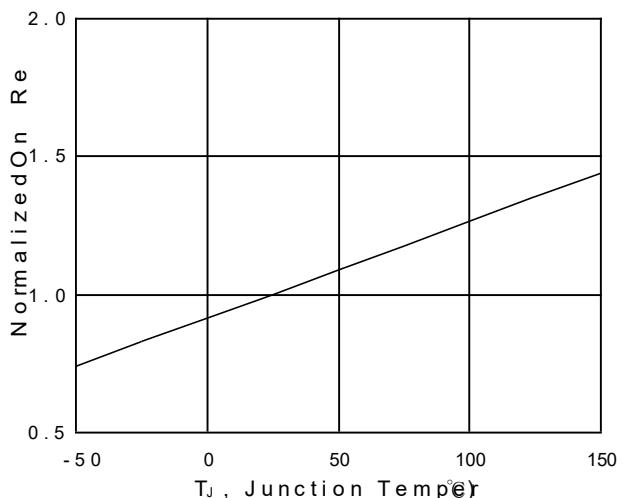


Fig.6 Normalized $R_{DS(on)}$ v.s T_J

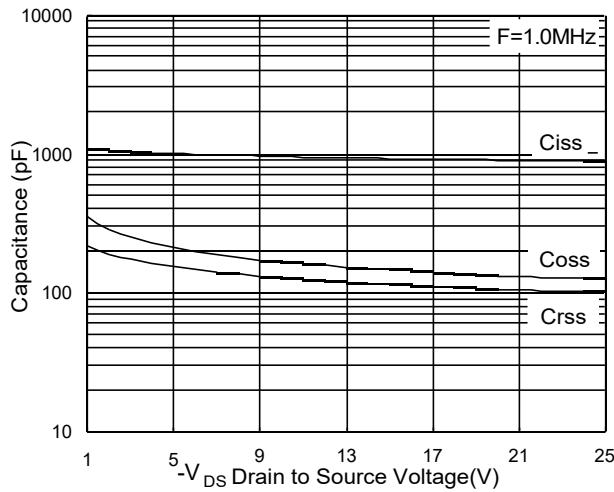


Fig.7 Capacitance

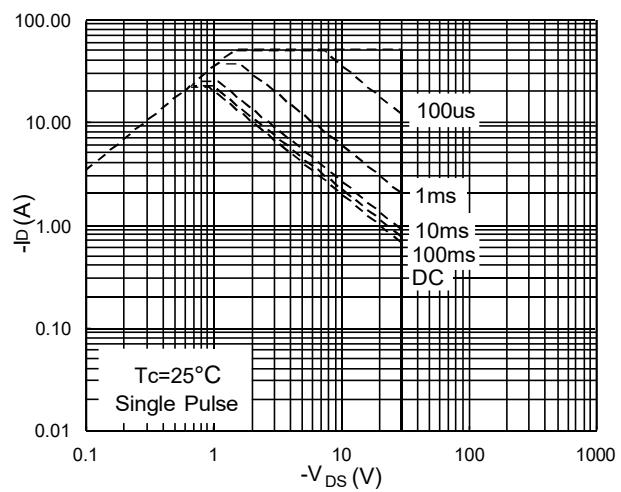


Fig.8 Safe Operating Area

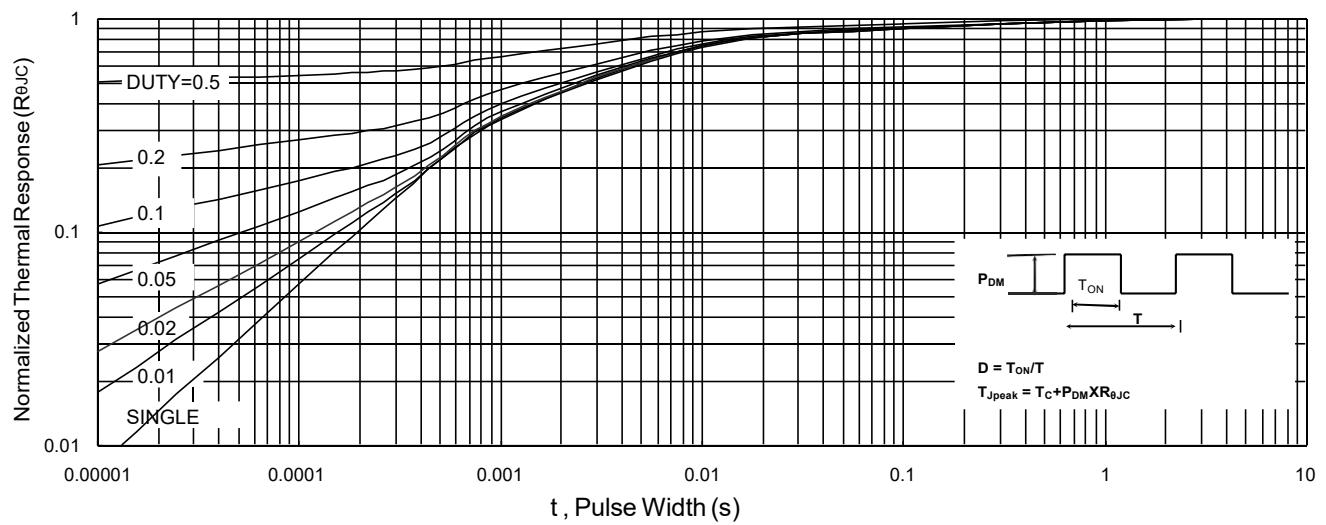


Fig.9 Normalized Maximum Transient Thermal Impedance

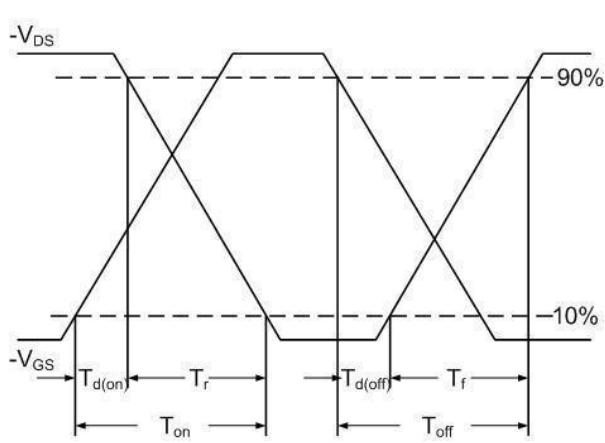


Fig.10 Switching Time Waveform

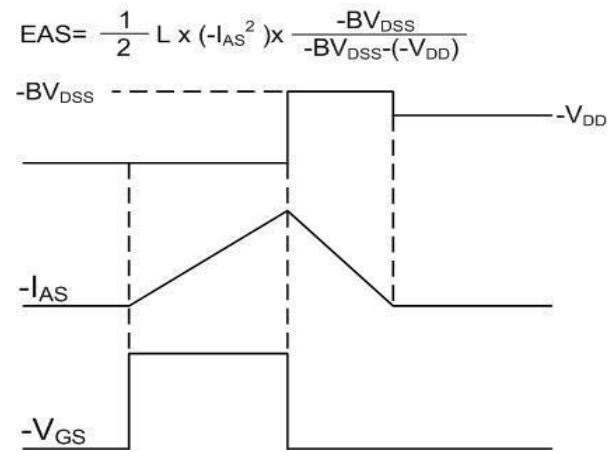
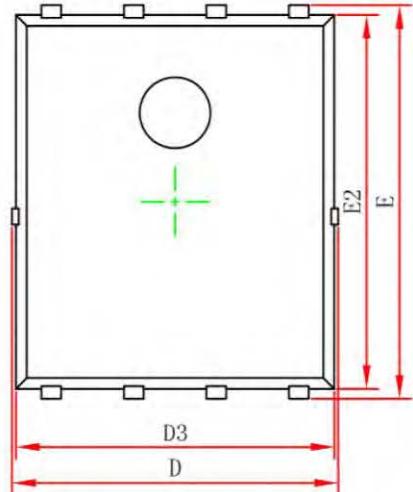


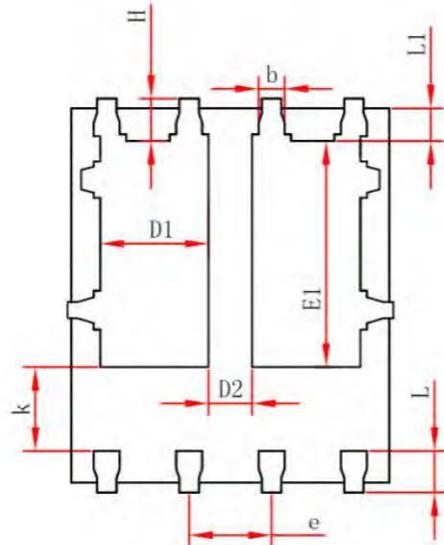
Fig.11 Unclamped Inductive Switching Waveform



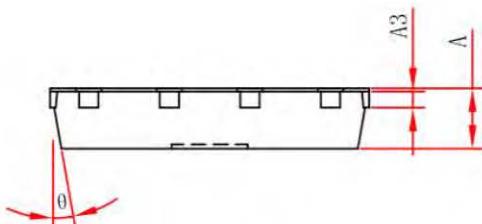
DFN5X6B-8L Package Information



Top View



Bottom View



Side View

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.154REF.		0.006REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	1.470	1.870	0.058	0.074
D2	0.470	0.870	0.019	0.034
E1	3.375	3.575	0.133	0.141
D3	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°	12°	10°	12°



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